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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are **Embedded - System On Chip (SoC)**?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions. SoCs combine a central

Details

Details	
Product Status	Obsolete
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	256KB
RAM Size	64KB
Peripherals	DMA, POR, WDT
Connectivity	EBI/EMI, Ethernet, I ² C, SPI, UART/USART
Speed	80MHz
Primary Attributes	ProASIC®3 FPGA, 200K Gates, 4608 D-Flip-Flops
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a2f200m3f-pq208i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

2 – SmartFusion DC and Switching Characteristics

General Specifications

Operating Conditions

Stresses beyond the operating conditions listed in Table 2-1 may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximum Ratings are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in Table 2-3 on page 2-3 is not implied.

Symbol	Parameter	Limits	Units
VCC	DC core supply voltage	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	V
VPP	Programming voltage	–0.3 to 3.75	V
VCCPLLx	Analog power supply (PLL)	–0.3 to 1.65	V
VCCFPGAIOBx	DC FPGA I/O buffer supply voltage	–0.3 to 3.75	V
VCCMSSIOBx	DC MSS I/O buffer supply voltage	–0.3 to 3.75	V
VI	I/O input voltage	–0.3 V to 3.6 V	V
		(when I/O hot insertion mode is enabled) -0.3 V to (VCCxxxxIOBx + 1 V) or 3.6 V, whichever voltage is lower (when I/O hot- insertion mode is disabled)	
VCC33A	Analog clean 3.3 V supply to the analog circuitry	-0.3 to 3.75	V
VCC33ADCx	Analog 3.3 V supply to ADC	-0.3 to 3.75	V
VCC33AP	Analog clean 3.3 V supply to the charge pump	-0.3 to 3.75	V
VCC33SDDx	Analog 3.3 V supply to the sigma-delta DAC	-0.3 to 3.75	V
VAREFx	Voltage reference for ADC	1.0 to 3.75	V
VCCRCOSC	Analog supply to the integrated RC oscillator	-0.3 to 3.75	V
VDDBAT	External battery supply	-0.3 to 3.75	V
VCCMAINXTAL	Analog supply to the main crystal oscillator	-0.3 to 3.75	V
VCCLPXTAL	Analog supply to the low power 32 kHz crystal oscillator	–0.3 to 3.75	V
VCCENVM	Embedded nonvolatile memory supply	-0.3 to 1.65	V
VCCESRAM	Embedded SRAM supply	–0.3 to 1.65	V
VCC15A	Analog 1.5 V supply to the analog circuitry	-0.3 to 1.65	V
VCC15ADCx	Analog 1.5 V supply to the ADC	-0.3 to 1.65	V
T _{STG} ¹	Storage temperature	–65 to +150	°C
T _J ¹	Junction temperature	125	°C

Table 2-1 • Absolute Maximum Ratings

Notes:

1. For flash programming and retention maximum limits, refer to Table 2-4 on page 2-4. For recommended operating conditions, refer to Table 2-3 on page 2-3.

2. The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in Table 2-5 on page 2-4.

	VCCMSSIOBx (V)	Static Power PDC7 (mW)	Dynamic Power PAC9 (µW/MHz)
Single-Ended	+ +		
3.3 V LVTTL / 3.3 V LVCMOS	3.3	_	17.21
3.3 V LVCMOS / 3.3 V LVCMOS – Schmitt trigger	3.3	_	20.00
2.5 V LVCMOS	2.5	_	5.55
2.5 V LVCMOS – Schmitt trigger	2.5	-	7.03
1.8 V LVCMOS	1.8	_	2.61
1.8 V LVCMOS – Schmitt trigger	1.8	-	2.72
1.5 V LVCMOS (JESD8-11)	1.5	_	1.98
1.5 V LVCMOS (JESD8-11) – Schmitt trigger	1.5	-	1.93

Table 2-11 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings Applicable to MSS I/O Banks

Table 2-12 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings^{*} Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

	C _{LOAD} (pF)	VCCFPGAIOBx (V)	Static Power PDC8 (mW)	Dynamic Power PAC10 (µW/MHz)
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	35	3.3	_	475.66
2.5 V LVCMOS	35	2.5	_	270.50
1.8 V LVCMOS	35	1.8	_	152.17
1.5 V LVCMOS (JESD8-11)	35	1.5	_	104.44
3.3 V PCI	10	3.3	_	202.69
3.3 V PCI-X	10	3.3	_	202.69
Differential				-
LVDS	-	2.5	7.74	88.26
LVPECL	_	3.3	19.54	164.99

Note: *Dynamic power consumption is given for standard load and software default drive strength and output slew.

Table 2-13 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings Applicable to MSS I/O Banks

	C _{LOAD} (pF)	VCCMSSIOBx (V)	Static Power PDC8 (mW) ²	Dynamic Power PAC10 (µW/MHz) ³
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	10	3.3	_	155.65
2.5 V LVCMOS	10	2.5	_	88.23
1.8 V LVCMOS	10	1.8	_	45.03
1.5 V LVCMOS (JESD8-11)	10	1.5	_	31.01

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SmartFusion DC and Switching Characteristics

Standby Mode and Time Keeping Mode

 $P_{NET} = 0 W$

I/O Input Buffer Dynamic Contribution—PINPUTS

SoC Mode

 $\mathsf{P}_{\mathsf{INPUTS}}$ = $\mathsf{N}_{\mathsf{INPUTS}}$ * $(\alpha_2$ / 2) * $\mathsf{P}_{\mathsf{AC9}}$ * $\mathsf{F}_{\mathsf{CLK}}$ Where:

N_{INPUTS} is the number of I/O input buffers used in the design.

 α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-17 on page 2-18.

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

P_{INPUTS} = 0 W

I/O Output Buffer Dynamic Contribution—POUTPUTS

SoC Mode

 $\mathsf{P}_{OUTPUTS} = \mathsf{N}_{OUTPUTS} * (\alpha_2 / 2) * \beta_1 * \mathsf{P}_{AC10} * \mathsf{F}_{CLK}$ Where:

N_{OUTPUTS} is the number of I/O output buffers used in the design.

 α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-17 on page 2-18.

 β_1 is the I/O buffer enable rate—guidelines are provided in Table 2-18 on page 2-18.

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

P_{OUTPUTS} = 0 W

FPGA Fabric SRAM Dynamic Contribution—P_{MEMORY}

SoC Mode

 $P_{MEMORY} = (N_{BLOCKS} * P_{AC11} * \beta_2 * F_{READ-CLOCK}) + (N_{BLOCKS} * P_{AC12} * \beta_3 * F_{WRITE-CLOCK})$ Where:

N_{BLOCKS} is the number of RAM blocks used in the design.

 $F_{READ-CLOCK}$ is the memory read clock frequency.

 β_2 is the RAM enable rate for read operations—guidelines are provided in Table 2-18 on page 2-18.

 β_3 the RAM enable rate for write operations—guidelines are provided in Table 2-18 on page 2-18. F_{WRITE-CLOCK} is the memory write clock frequency.

Standby Mode and Time Keeping Mode

P_{MEMORY} = 0 W

PLL/CCC Dynamic Contribution—P_{PLL}

SoC Mode

P_{PLL} = P_{AC13} * F_{CLKOUT}

F_{CLKIN} is the input clock frequency.

F_{CLKOUT} is the output clock frequency.¹

Standby Mode and Time Keeping Mode

^{1.} The PLL dynamic contribution depends on the input clock frequency, the number of output clock signals generated by the PLL, and the frequency of each output clock. If a PLL is used to generate more than one output clock, include each output clock in the formula output clock by adding its corresponding contribution (P_{AC14} * F_{CLKOUT} product) to the total PLL contribution.

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-19 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial Conditions—Software Default Settings Applicable to FPGA I/O Banks

				VIL	VIH		VOL	VOH	I _{OL} ¹	I _{OH} 1
I/O Standard	Drive Strgth.			Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	High	-0.3	0.8	2	3.6	0.4	2.4	12	12
2.5 V LVCMOS	12 mA	High	-0.3	0.7	1.7	3.6	0.7	1.7	12	12
1.8 V LVCMOS	12 mA	High	-0.3	0.35 * VCCxxxxIOBx	0.65* VCCxxxxIOBx	3.6	0.45	VCCxxxxIOBx - 0.45	12	12
1.5 V LVCMOS	12 mA	High	-0.3	0.35 * VCCxxxxIOBx	0.65* VCCxxxxIOBx	3.6	0.25 * VCCxxxxIOBx	0.75* VCCxxxxIOBx	12	12
3.3 V PCI	Per PCI specifications									
3.3 V PCI-X		Per PCI-X specifications								

Notes:

1. Currents are measured at 85°C junction temperature.

2. Output slew rate can be extracted by the IBIS Models.

Table 2-20 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial Conditions—Software Default Settings Applicable to MSS I/O Banks

			VIL		VIH		VOL	VOH	I _{OL} ¹	I _{OH} 1
I/O Standard	Drive Strgth.	Slew Rate		Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	High	-0.3	0.8	2	3.6	0.4	2.4	8	8
2.5 V LVCMOS	8 mA	High	-0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	High	-0.3	0.35* VCCxxxxIOBx	0.65* VCCxxxxIOBx	3.6	0.45	VCCxxxxIOBx - 0.45	4	4
1.5 V LVCMOS	2 mA	High	-0.3	0.35* VCCxxxxIOBx	0.65* VCCxxxxIOBx	3.6	0.25* VCCxxxxIOBx	0.75* VCCxxxxIOBx	2	2

Notes:

1. Currents are measured at 85°C junction temperature.

2. Output slew rate can be extracted by the IBIS Models.

Timing Characteristics

Table 2-38 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew

Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V, Worst-Case VCCxxxxIOBx = 3.0 V Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{zLS}	t _{zHS}	Units
4 mA	Std.	0.60	7.20	0.04	0.97	0.39	7.34	6.18	2.52	2.46	9.39	8.23	ns
	-1	0.50	6.00	0.03	0.81	0.32	6.11	5.15	2.10	2.05	7.83	6.86	ns
8 mA	Std.	0.60	4.64	0.04	0.97	0.39	4.73	3.84	2.85	3.02	6.79	5.90	ns
	-1	0.50	3.87	0.03	0.81	0.32	3.94	3.20	2.37	2.52	5.65	4.91	ns
12 mA	Std.	0.60	3.37	0.04	0.97	0.39	3.43	2.67	3.07	3.39	5.49	4.73	ns
	-1	0.50	2.81	0.03	0.81	0.32	2.86	2.23	2.55	2.82	4.58	3.94	ns
16 mA	Std.	0.60	3.18	0.04	0.97	0.39	3.24	2.43	3.11	3.48	5.30	4.49	ns
	-1	0.50	2.65	0.03	0.81	0.32	2.70	2.03	2.59	2.90	4.42	3.74	ns
24 mA	Std.	0.60	2.93	0.04	0.97	0.39	2.99	2.03	3.17	3.83	5.05	4.09	ns
	-1	0.50	2.45	0.03	0.81	0.32	2.49	1.69	2.64	3.19	4.21	3.41	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

Table 2-39 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew

Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V, Worst-Case VCCxxxxIOBx = 3.0 V Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{zLS}	t _{zHS}	Units
4 mA	Std.	0.60	9.75	0.04	0.97	0.39	9.93	8.22	2.52	2.31	11.99	10.28	ns
	-1	0.50	8.12	0.03	0.81	0.32	8.27	6.85	2.10	1.93	9.99	8.57	ns
8 mA	Std.	0.60	6.96	0.04	0.97	0.39	7.09	5.85	2.84	2.87	9.15	7.91	ns
	-1	0.50	5.80	0.03	0.81	0.32	5.91	4.88	2.37	2.39	7.62	6.59	ns
12 mA	Std.	0.60	5.35	0.04	0.97	0.39	5.45	4.58	3.06	3.23	7.51	6.64	ns
	-1	0.50	4.46	0.03	0.81	0.32	4.54	3.82	2.55	2.69	6.26	5.53	ns
16 mA	Std.	0.60	5.01	0.04	0.97	0.39	5.10	4.30	3.11	3.32	7.16	6.36	ns
	-1	0.50	4.17	0.03	0.81	0.32	4.25	3.58	2.59	2.77	5.97	5.30	ns
24 mA	Std.	0.60	4.67	0.04	0.97	0.39	4.75	4.28	3.16	3.66	6.81	6.34	ns
	-1	0.50	3.89	0.03	0.81	0.32	3.96	3.57	2.64	3.05	5.68	5.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

Table 2-40 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew

Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V, Worst-Case VCCxxxxIOBx = 3.0 V Applicable to MSS I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{zL}	t _{zH}	t _{LZ}	t _{HZ}	Units
8 mA	Std.	0.22	2.31	0.09	0.94	1.30	0.22	2.35	1.86	2.20	2.45	ns
	-1	0.18	1.92	0.07	0.78	1.09	0.18	1.96	1.55	1.83	2.04	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t _{oclkq}	Clock-to-Q of the Output Data Register	HH, DOUT
tosud	Data Setup Time for the Output Data Register	FF, HH
t _{ОНD}	Data Hold Time for the Output Data Register	FF, HH
tosue	Enable Setup Time for the Output Data Register	GG, HH
t _{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t _{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
t _{OREMCLR}	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
t _{ORECCLR}	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t _{oeclkq}	Clock-to-Q of the Output Enable Register	HH, EOUT
tOESUD	Data Setup Time for the Output Enable Register	JJ, HH
t _{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
tOESUE	Enable Setup Time for the Output Enable Register	KK, HH
t _{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
t _{OECLR2Q}	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
t _{OEREMCLR}	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
t _{OERECCLR}	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t _{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t _{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t _{IHD}	Data Hold Time for the Input Data Register	CC, AA
t _{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t _{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t _{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
t _{IREMCLR}	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
t _{IRECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

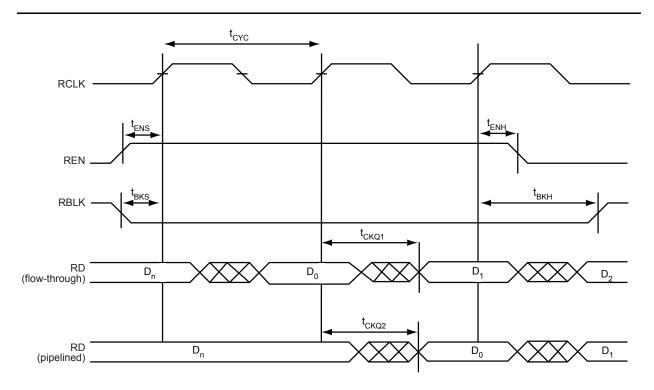
Table 2-70 • Parameter Definition and Measuring Nodes

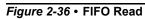
* See Figure 2-15 on page 2-46 for more information.

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SmartFusion DC and Switching Characteristics

Timing Waveforms





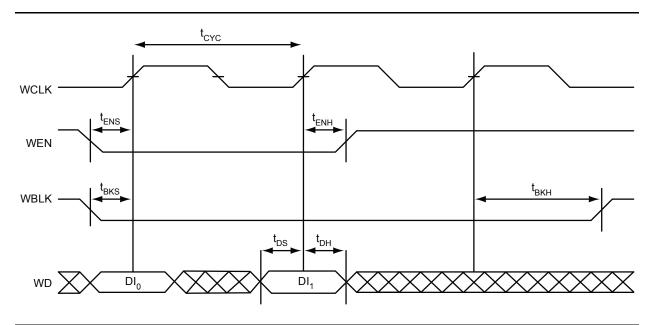


Figure 2-37 • FIFO Write

Temperature Monitor

Unless otherwise noted, temperature monitor performance is specified with a 2N3904 diode-connected bipolar transistor from National Semiconductor or Infineon Technologies, nominal power supply voltages, with the output measured using the internal voltage reference with the internal ADC in 12-bit mode and 62.5 Ksps. After digital compensation. Unless otherwise noted, the specifications pertain to conditions where the SmartFusion cSoC and the sensing diode are at the same temperature.

Table 2-94 • Temperature Monitor Performance Specifications

Specification	Test Conditions	Min.	Typical	Max.	Units
Input diode temperature range		-55		150	°C
		233.2		378.15	K
Temperature sensitivity			2.5		mV/K
Intercept	Extrapolated to 0K		0		V
Input referred temperature offset error	At 25°C (298.15K)		±1	1.5	°C
Gain error	Slope of BFSL vs. 2.5 mV/K		±1	2.5	% nom.
Overall accuracy	Peak error from ideal transfer function		±2	±3	°C
Input referred noise	At 25°C (298.15K) – no output averaging		4		°C rms
Output current	Idle mode		100		μA
	Final measurement phases		10		μA
Analog settling time	Measured to 0.1% of final value, (with ADC load)				
	From TM_STB (High)	5			μs
	From ADC_START (High)	5		105	μs
AT parasitic capacitance				500	pF
Power supply rejection ratio	DC (0–10 KHz)	1.2	0.7		°C/V
Input referred temperature sensitivity error	Variation due to device temperature (-40°C to +100°C). External temperature sensor held constant.		0.005	0.008	°C/°C
Temperature monitor (TM)	VCC33A		200		μA
operational power supply current requirements (per temperature	VCC33AP		150		μA
monitor instance, not including ADC or VAREFx)	VCC15A		50		μA

Note: All results are based on averaging over 64 samples.

Inter-Integrated Circuit (I²C) Characteristics

This section describes the DC and switching of the I^2C interface. Unless otherwise noted, all output characteristics given are for a 100 pF load on the pins. For timing parameter definitions, refer to Figure 2-48 on page 2-92.

Parameter	Definition	Condition	Value	Unit
V _{IL}	Minimum input low voltage	_	SeeTable 2-36 on page 2-30	-
	Maximum input low voltage	-	See Table 2-36	_
V _{IH}	Minimum input high voltage	_	See Table 2-36	-
	Maximum input high voltage	_	See Table 2-36	-
V _{OL}	Maximum output voltage low	I _{OL} = 8 mA	See Table 2-36	-
I _{IL}	Input current high	_	See Table 2-36	-
I _{IH}	Input current low	_	See Table 2-36	-
V _{hyst}	Hysteresis of Schmitt trigger inputs	_	See Table 2-33 on page 2-29	V
T _{FALL}	Fall time ²	VIHmin to VILMax, C _{load} = 400 pF	15.0	ns
		VIHmin to VILMax, C _{load} = 100 pF	4.0	ns
T _{RISE}	Rise time ²	VILMax to VIHmin, C _{load} = 400pF	19.5	ns
		VILMax to VIHmin, C _{load} = 100pF	5.2	ns
Cin	Pin capacitance	VIN = 0, f = 1.0 MHz	8.0	pF
R _{pull-up}	Output buffer maximum pull- down Resistance ¹	_	50	Ω
R _{pull-down}	Output buffer maximum pull-up Resistance ¹	_	150	Ω
D _{max}	Maximum data rate	Fast mode	400	Kbps
t _{LOW}	Low period of I2C_x_SCL ³	_	1	pclk cycles
t _{HIGH}	High period of I2C_x_SCL ³	_	1	pclk cycles
t _{HD;STA}	START hold time ³	_	1	pclk cycles
t _{SU;STA}	START setup time ³	_	1	pclk cycles
t _{HD;DAT}	DATA hold time ³	_	1	pclk cycles
t _{SU;DAT}	DATA setup time ³		1	pclk cycles

Table 2-101 • I²C Characteristics

Commercial Case Conditions: T_J = 85°C, V_{DD} = 1.425 V, -1 Speed Grade

Notes:

1. These maximum values are provided for information only. Minimum output buffer resistance values depend on VCCxxxxIOBx, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the SoC Products Group website at http://www.microsemi.com/index.php?option=com_microsemi<emid=489&lang=en&view=salescontact.

 These values are provided for a load of 100 pF and 400 pF. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the SoC Products Group website at http://www.microsemi.com/index.php?option=com_microsemi&Itemid=489&Iang=en&view=salescontact.

3. For allowable Pclk configurations, refer to the Inter-Integrated Circuit (I²C) Peripherals section in the SmartFusion Microcontroller Subsystem User's Guide.



Pin Descriptions

Special Function Pins

Name	Туре	Polarity/Bus Size	Description
NC			No connect
			This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.
DC			Do not connect.
			This pin should not be connected to any signals on the PCB. These pins should be left unconnected.
LPXIN	In	1	Low power 32 KHz crystal oscillator.
			Input from the 32 KHz oscillator. Pin for connecting a low power 32 KHz watch crystal. If not used, the LPXIN pin can be left floating. For more information, see the PLLs, Clock Conditioning Circuitry, and On-Chip Crystal Oscillators section in the <i>SmartFusion Microcontroller Subsystem User's Guide</i> .
LPXOUT	In	1	Low power 32 KHz crystal oscillator.
			Output to the 32 KHz oscillator. Pin for connecting a low power 32 KHz watch crystal. If not used, the LPXOUT pin can be left floating. For more information, see the PLLs, Clock Conditioning Circuitry, and On-Chip Crystal Oscillators section in the <i>SmartFusion Microcontroller Subsystem User's Guide</i> .
MAINXIN	In	1	Main crystal oscillator circuit.
			Input to the crystal oscillator circuit. Pin for connecting an external crystal, ceramic resonator, or RC network. When using an external crystal or ceramic oscillator, external capacitors are also recommended. Refer to documentation from the crystal oscillator manufacturer for proper capacitor value.
			If an external RC network or clock input is used, the RC components are connected to the MAINXIN pin, with MAINXOUT left floating. When the main crystal oscillator is not being used, MAINXIN and MAINXOUT pins can be left floating.
			For more information, see the PLLs, Clock Conditioning Circuitry, and On-Chip Crystal Oscillators section in the <i>SmartFusion Microcontroller Subsystem User's Guide</i> .
MAINXOUT	Out	1	Main crystal oscillator circuit.
			Output from the crystal oscillator circuit. Pin for connecting external crystal or ceramic resonator. When using an external crystal or ceramic oscillator, external capacitors are also recommended. Refer to documentation from the crystal oscillator manufacturer for proper capacitor value.
			If an external RC network or clock input is used, the RC components are connected to the MAINXIN pin, with MAINXOUT left floating. When the main crystal oscillator is not being used, MAINXIN and MAINXOUT pins can be left floating.
			For more information, see the PLLs, Clock Conditioning Circuitry, and On-Chip Crystal Oscillators section in the <i>SmartFusion Microcontroller Subsystem User's Guide</i> .

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SmartFusion Customizable System-on-Chip (cSoC)

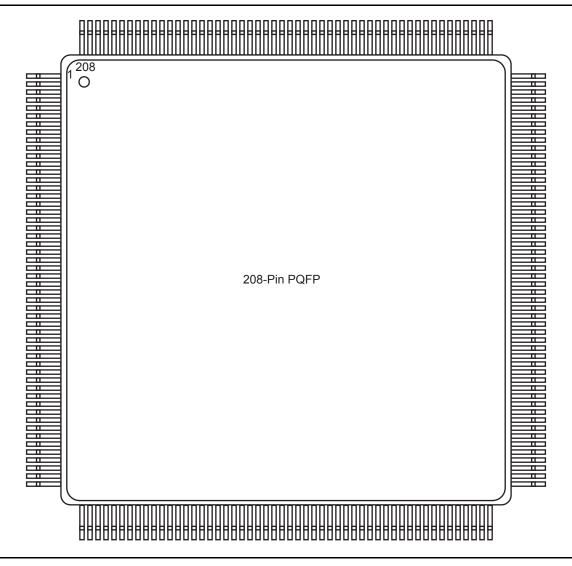
Pin	CS288				
No.	A2F060 Function	A2F200 Function	A2F500 Function		
K17	GNDLPXTAL	GNDLPXTAL	GNDLPXTAL		
K19	GNDMAINXTAL	GNDMAINXTAL	GNDMAINXTAL		
K21	MAINXIN	MAINXIN	MAINXIN		
L1	GNDRCOSC	GNDRCOSC	GNDRCOSC		
L3	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5		
L5	EMC_DB[2]/IO37NPB5V0	EMC_DB[2]/IO60NPB5V0	EMC_DB[2]/IO77NPB5V0		
L6	NC	GNDQ	GNDQ		
L8	VCC	VCC	VCC		
L9	GND	GND	GND		
L10	VCC	VCC	VCC		
L12	VCC	VCC	VCC		
L13	GND	GND	GND		
L14	VCC	VCC	VCC		
L16	VCCLPXTAL	VCCLPXTAL	VCCLPXTAL		
L17	VDDBAT	VDDBAT	VDDBAT		
L19	LPXIN	LPXIN	LPXIN		
L21	MAINXOUT	MAINXOUT	MAINXOUT		
M1	VCCRCOSC	VCCRCOSC	VCCRCOSC		
M3	MSS_RESET_N	MSS_RESET_N	MSS_RESET_N		
M5	GPIO_5/IO28RSB4V0	GPIO_5/IO42RSB4V0	GPIO_5/IO51RSB4V0		
M6	GND	GND	GND		
M8	GND	GND	GND		
M9	VCC	VCC	VCC		
M10	GND	GND	GND		
M11	VCC	VCC	VCC		
M12	GND	GND	GND		
M13	VCC	VCC	VCC		
M14	GND	GND	GND		
M16	TMS	TMS	TMS		
M17	VJTAG	VJTAG	VJTAG		
M19	TDO	TDO	TDO		

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.



PQ208



Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx.



	PQ208		
Pin Number	A2F200	A2F500	
94	ABPS5	ABPS5	
95	ABPS4	ABPS4	
96	GNDAQ	GNDAQ	
97	GNDA	GNDA	
98	NC	NC	
99	GNDVAREF	GNDVAREF	
100	VAREFOUT	VAREFOUT	
101	PU_N	PU_N	
102	VCC33A	VCC33A	
103	PTEM	PTEM	
104	PTBASE	PTBASE	
105	SPI_0_DO/GPIO_16	SPI_0_DO/GPIO_16	
106	SPI_0_DI/GPIO_17	SPI_0_DI/GPIO_17	
107	SPI_0_CLK/GPIO_18	SPI_0_CLK/GPIO_18	
108	SPI_0_SS/GPIO_19	SPI_0_SS/GPIO_19	
109	UART_0_RXD/GPIO_21	UART_0_RXD/GPIO_21	
110	UART_0_TXD/GPIO_20	UART_0_TXD/GPIO_20	
111	UART_1_RXD/GPIO_29	UART_1_RXD/GPIO_29	
112	UART_1_TXD/GPIO_28	UART_1_TXD/GPIO_28	
113	VCC	VCC	
114	VCCMSSIOB2	VCCMSSIOB2	
115	GND	GND	
116	I2C_1_SDA/GPIO_30	I2C_1_SDA/GPIO_30	
117	I2C_1_SCL/GPIO_31	I2C_1_SCL/GPIO_31	
118	I2C_0_SDA/GPIO_22	I2C_0_SDA/GPIO_22	
119	I2C_0_SCL/GPIO_23	I2C_0_SCL/GPIO_23	
120	GNDENVM	GNDENVM	
121	VCCENVM	VCCENVM	
122	JTAGSEL	JTAGSEL	
123	ТСК	тск	
124	TDI	TDI	

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.

FG256 Pin A2F060 Function A2F200 Function A2F500 Function No. GNDQ GNDQ GNDQ B16 C1 EMC DB[14]/IO45NDB5V0 EMC DB[14]/GAB2/IO71NDB5V0 EMC DB[14]/GAB2/IO88NDB5V0 **VCCPLL0** VCCPLL VCCPLL0 C2 EMC BYTEN[0]/GAC0/IO02NDB0V0 EMC BYTEN[0]/GAC0/IO07NDB0V0 C3 EMC BYTEN[0]/IO02NDB0V0 VCCFPGAIOB0 VCCFPGAIOB0 VCCFPGAIOB0 C4 EMC CS0 N/GAB0/IO05NDB0V0 C5 EMC CS0 N/IO01NDB0V0 EMC CS0 N/GAB0/IO01NDB0V0 EMC CS1 N/IO01PDB0V0 EMC CS1 N/GAB1/IO01PDB0V0 EMC CS1 N/GAB1/IO05PDB0V0 C6 C7 GND GND GND EMC AB[8]/IO08NDB0V0 EMC AB[8]/IO08NDB0V0 EMC AB[8]/IO13NDB0V0 C8 EMC AB[11]/IO09PDB0V0 EMC AB[11]/IO09PDB0V0 EMC AB[11]/IO11PDB0V0 C9 VCCFPGAIOB0 VCCFPGAIOB0 VCCFPGAIOB0 C10 C11 EMC AB[17]/IO12PDB0V0 EMC AB[17]/IO12PDB0V0 EMC AB[17]/IO17PDB0V0 EMC AB[19]/IO13PDB0V0 C12 EMC AB[19]/IO13PDB0V0 EMC AB[19]/IO18PDB0V0 C13 GND GND GND C14 GCC0/IO18NPB0V0 GBA2/IO20PPB1V0 GBA2/IO27PPB1V0 C15 GCB0/IO19NDB0V0 GCA2/IO23PDB1V0 GCA2/IO28PDB1V0 * C16 GCB1/IO19PDB0V0 IO23NDB1V0 IO28NDB1V0 D1 VCCFPGAIOB5 VCCFPGAIOB5 VCCFPGAIOB5 D2 VCOMPLA0 **VCOMPLA** VCOMPLA0 GND GND D3 GND D4 GNDQ GNDQ GNDQ D5 EMC CLK/IO00NDB0V0 EMC CLK/GAA0/IO00NDB0V0 EMC CLK/GAA0/IO02NDB0V0 D6 EMC RW N/IO00PDB0V0 EMC RW N/GAA1/IO00PDB0V0 EMC RW N/GAA1/IO02PDB0V0 EMC_AB[6]/IO07NDB0V0 EMC AB[6]/IO07NDB0V0 EMC AB[6]/IO12NDB0V0 D7 D8 EMC AB[7]/IO07PDB0V0 EMC AB[7]/IO07PDB0V0 EMC AB[7]/IO12PDB0V0 EMC AB[10]/IO09NDB0V0 EMC AB[10]/IO09NDB0V0 EMC AB[10]/IO11NDB0V0 D9 D10 EMC AB[22]/IO15NDB0V0 EMC AB[22]/IO15NDB0V0 EMC AB[22]/IO19NDB0V0 EMC AB[23]/IO15PDB0V0 EMC AB[23]/IO15PDB0V0 EMC AB[23]/IO19PDB0V0 D11 D12 GNDQ GNDQ GNDQ GCC1/IO18PPB0V0 GBB2/IO20NPB1V0 GBB2/IO27NPB1V0 D13 D14 GCA0/IO20NDB0V0 GCB2/IO24PDB1V0 GCB2/IO33PDB1V0

Notes:

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Pin Descriptions

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.

SmartFusion Customizable System-on-Chip (cSoC)

Pin	FG256				
No.	A2F060 Function	A2F200 Function	A2F500 Function		
M11	ADC6	TM2	TM2		
M12	ADC5	CM2	CM2		
M13	SPI_0_SS/GPIO_19	SPI_0_SS/GPIO_19	SPI_0_SS/GPIO_19		
M14	VCCMSSIOB2	VCCMSSIOB2	VCCMSSIOB2		
M15	SPI_0_CLK/GPIO_18	SPI_0_CLK/GPIO_18	SPI_0_CLK/GPIO_18		
M16	SPI_0_DI/GPIO_17	SPI_0_DI/GPIO_17	SPI_0_DI/GPIO_17		
N1	GPIO_8/IO25RSB4V0	MAC_RXD[1]/IO53RSB4V0	MAC_RXD[1]/IO62RSB4V0		
N2	VCCMSSIOB4	VCCMSSIOB4	VCCMSSIOB4		
N3	VCC15A	VCC15A	VCC15A		
N4	VCC33AP	VCC33AP	VCC33AP		
N5	NC	ABPS3	ABPS3		
N6	ADC4	TM1	TM1		
N7	NC	GND33ADC0	GND33ADC0		
N8	VCC33ADC0	VCC33ADC1	VCC33ADC1		
N9	ADC8	ADC5	ADC5		
N10	CM0	CM3	CM3		
N11	GNDAQ	GNDAQ	GNDAQ		
N12	VAREFOUT	VAREFOUT	VAREFOUT		
N13	NC	GNDSDD1	GNDSDD1		
N14	NC	VCC33SDD1	VCC33SDD1		
N15	GND	GND	GND		
N16	SPI_0_DO/GPIO_16	SPI_0_DO/GPIO_16	SPI_0_DO/GPIO_16		
P1	GNDSDD0	GNDSDD0	GNDSDD0		
P2	VCC33SDD0	VCC33SDD0	VCC33SDD0		
P3	VCC33N	VCC33N	VCC33N		
P4	GNDA	GNDA	GNDA		
P5	GNDAQ	GNDAQ	GNDAQ		
P6	NC	CM1	CM1		
P7	NC	ADC2	ADC2		
P8	NC	VCC15ADC0	VCC15ADC0		
P9	ADC9	ADC6	ADC6		

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.

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SmartFusion Customizable System-on-Chip (cSoC)

Pin		FG256		
No.	A2F060 Function	A2F200 Function	A2F500 Function	
Т9	VAREF0	VAREF1	VAREF1	
T10	ABPS0	ABPS6	ABPS6	
T11	NC	ABPS5	ABPS5	
T12	NC	SDD1	SDD1	
T13	GNDVAREF	GNDVAREF	GNDVAREF	
T14	GNDMAINXTAL	GNDMAINXTAL	GNDMAINXTAL	
T15	VCCLPXTAL	VCCLPXTAL	VCCLPXTAL	
T16	PU_N	PU_N	PU_N	

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.

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SmartFusion Customizable System-on-Chip (cSoC)

	FG484		
Pin Number	A2F200 Function	A2F500 Function	
H7	GND	GND	
H8	VCC	VCC	
H9	GND	GND	
H10	VCC	VCC	
H11	GND	GND	
H12	VCC	VCC	
H13	GND	GND	
H14	VCC	VCC	
H15	GND	GND	
H16	VCCFPGAIOB1	VCCFPGAIOB1	
H17	IO25NDB1V0	IO29NDB1V0	
H18	GCC2/IO25PDB1V0	GCC2/IO29PDB1V0	
H19	GND	GND	
H20	GCC0/IO26NPB1V0	GCC0/IO35NPB1V0	
H21	VCCFPGAIOB1	VCCFPGAIOB1	
H22	GCB0/IO27NDB1V0	GCB0/IO34NDB1V0	
J1	EMC_DB[6]/GEB0/IO62NDB5V0	EMC_DB[6]/GEB0/IO79NDB5V0	
J2	EMC_DB[5]/GEA1/IO61PDB5V0	EMC_DB[5]/GEA1/IO78PDB5V0	
J3	EMC_DB[4]/GEA0/IO61NDB5V0	EMC_DB[4]/GEA0/IO78NDB5V0	
J4	EMC_DB[3]/GEC2/IO60PPB5V0	EMC_DB[3]/GEC2/IO77PPB5V0	
J5	VCCFPGAIOB5	VCCFPGAIOB5	
J6	GFA0/IO64NDB5V0	GFA0/IO81NDB5V0	
J7	VCCFPGAIOB5	VCCFPGAIOB5	
J8	GND	GND	
J9	VCC	VCC	
J10	GND	GND	
J11	VCC	VCC	
J12	GND	GND	
J13	VCC	VCC	
J14	GND	GND	
J15	VCC	VCC	
J16	GND	GND	
J17	NC	IO37PDB1V0	
J18	VCCFPGAIOB1	VCCFPGAIOB1	

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.



	FG484		
Pin Number	A2F200 Function	A2F500 Function	
T1	GND	GND	
T2	VCCMSSIOB4	VCCMSSIOB4	
Т3	GPIO_8/IO39RSB4V0	GPIO_8/IO48RSB4V0	
T4	GPIO_11/IO57RSB4V0	GPIO_11/IO66RSB4V0	
T5	GND	GND	
Т6	MAC_CLK	MAC_CLK	
Τ7	VCCMSSIOB4	VCCMSSIOB4	
Т8	VCC33SDD0	VCC33SDD0	
Т9	VCC15A	VCC15A	
T10	GNDAQ	GNDAQ	
T11	GND33ADC0	GND33ADC0	
T12	ADC7	ADC7	
T13	NC	TM4	
T14	NC	VAREF2	
T15	VAREFOUT	VAREFOUT	
T16	VCCMSSIOB2	VCCMSSIOB2	
T17	SPI_1_DO/GPIO_24	SPI_1_DO/GPIO_24	
T18	GND	GND	
T19	NC	NC	
T20	NC	NC	
T21	VCCMSSIOB2	VCCMSSIOB2	
T22	GND	GND	
U1	GND	GND	
U2	GPIO_5/IO42RSB4V0	GPIO_5/IO51RSB4V0	
U3	GPIO_10/IO58RSB4V0	GPIO_10/IO67RSB4V0	
U4	VCCMSSIOB4	VCCMSSIOB4	
U5	MAC_RXD[1]/IO53RSB4V0	MAC_RXD[1]/IO62RSB4V0	
U6	NC	NC	
U7	VCC33AP	VCC33AP	
U8	VCC33N	VCC33N	
U9	CM1	CM1	
U10	VAREF0	VAREF0	
U11	GND33ADC1	GND33ADC1	
U12	ADC4	ADC4	

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.

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SmartFusion Customizable System-on-Chip (cSoC)

Revision	Changes	Page
Revision 5 (continued)	Available values for the Std. speed were added to the timing tables from Table 2-38 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew to Table 2-92 • JTAG 1532 (SAR 29331).	2-31 to 2-76
	One or more values changed for the –1 speed in tables covering 3.3 V LVCMOS, 2.5 V LVCMOS, 1.8 V LVCMOS, 1.5 V LVCMOS, Combinatorial Cell Propagation Delays, and A2F200 Global Resources.	
	Table 2-80 • A2F500 Global Resource is new.	2-60
	Table 2-90 • eNVM Block Timing, Worst Commercial Case Conditions: $T_J = 85^{\circ}C$, VCC = 1.425 V was revised (SAR 27585).	2-76
	The programmable analog specifications tables were revised with updated information.	2-78 to 2-87
	Table 4-1 • Supported JTAG Programming Hardware was revised by adding a note to indicate "planned support" for several of the items in the table.	4-7
	The note on JTAGSEL in the "In-System Programming" section was revised to state that SoftConsole selects the appropriate TAP controller using the CTXSELECT JTAG command. When using SoftConsole, the state of JTAGSEL is a "don't care" (SAR 29261).	4-7
	The "CS288" and "FG256" pin tables for A2F060 are new, comparing the A2F060 function with the A2F200 function (SAR 29353).	5-24
	The "Handling When Unused" column was removed from the "FG256" pin table for A2F200 and A2F500 (SAR 29691).	5-42
Revision 4 (September 2010)	Table 2-8 • Power Supplies Configuration was revised. VCCRCOSC was moved to a column of its own with new values. VCCENVM was added to the table. Standby mode for VJTAG and VPP was changed from 0 V to N/A. "Disable" was changed to "Off" in the eNVM column. The column for RCOSC was deleted.	2-10
	The "Power-Down and Sleep Mode Implementation" section was revised to include VCCROSC.	2-11
Revision 3 (September 2010)	The "I/Os and Operating Voltage" section was revised to list "single 3.3 V power supply with on-chip 1.5 V regulator" and "external 1.5 V is allowed" (SAR 27663).	I
	The CS288 package was added to the "Package I/Os: MSS + FPGA I/Os" table (SAR 27101), "Product Ordering Codes" table, and "Temperature Grade Offerings" table (SAR 27044). The number of direct analog inputs for the FG256 package in A2F060 was changed from 8 to 6.	III, VI, VI
	Two notes were added to the "SmartFusion cSoC Family Product Table" indicating limitations for features of the A2F500 device:	II
	Two PLLs are available in CS288 and FG484 (one PLL in FG256). [ADCs, DACs, SCBs, comparators, current monitors, and bipolar high voltage monitors are] Available on FG484 only. FG256 and CS288 packages offer the same programmable analog capabilities as A2F200.	
	Table cells were merged in rows containing the same values for easier reading (SAR 24748).	
	The security feature option was added to the "Product Ordering Codes" table.	VI



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